



Cryogenic Operation of Silicon Detectors

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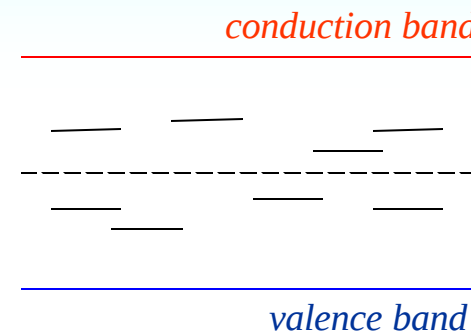
Outline

- The "*Lazarus effect*"
- Operation at Cryogenic Temperatures
- First Application: the RD39/NA60 Beamscope
- Q&A Issues
- Conclusions



Radiation Damage in Si

- Radiation generates lattice displacements
- Defects appear as energy levels in the forbidden band gap
- Leakage current increases with dose
 - increase of noise
 - power dissipation in the sensor
- Trapping and de-trapping of carriers
 - signal loss
 - ✓ Fraction of defects are filled and therefore charged, so they contribute to the **effective doping concentration** N_{eff}
 - ✓ Under irradiation, space charge becomes more and more negative
 - dramatic **increase of depletion voltage** ($V_{dep} \propto |N_{eff}|$)
 - signal loss
- **Annealing**: N_{eff} changes also after irradiation
 - need to keep the detector at -10°C





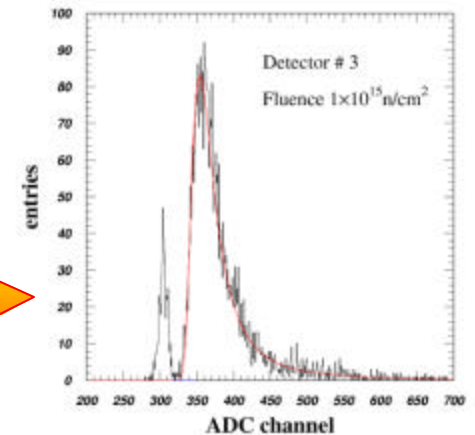
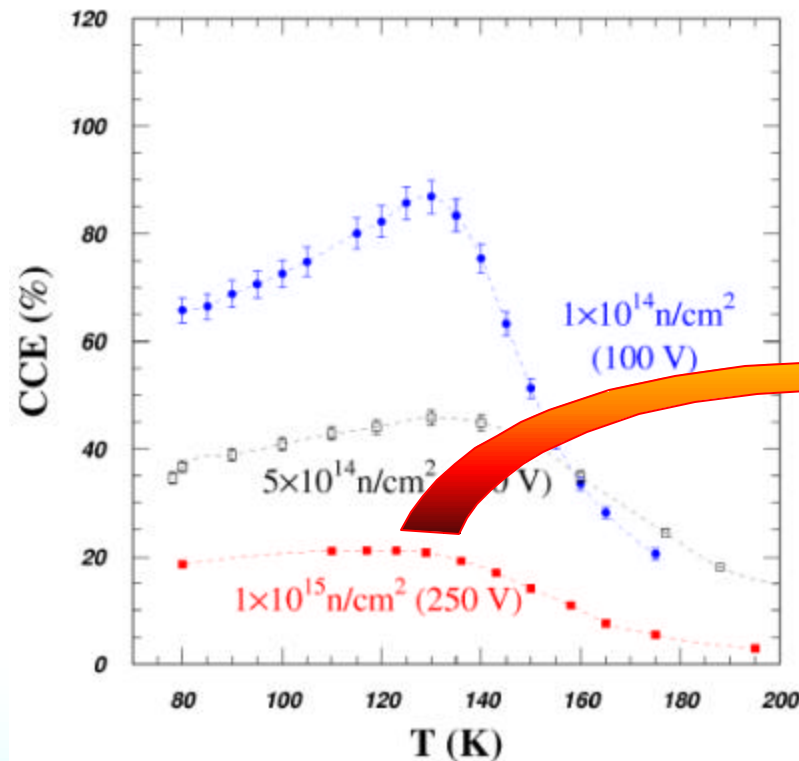
CCE vs Temperature

- Experimental observation: heavily irradiated Si detector no longer operational at room temperature “resuscitate” when cooled down to cryogenic temperatures

RD39 data

irradiated Si diodes
exposed to mips

$$CCE \equiv \frac{Q_{\text{measured}}}{Q_{\text{generated}}}$$

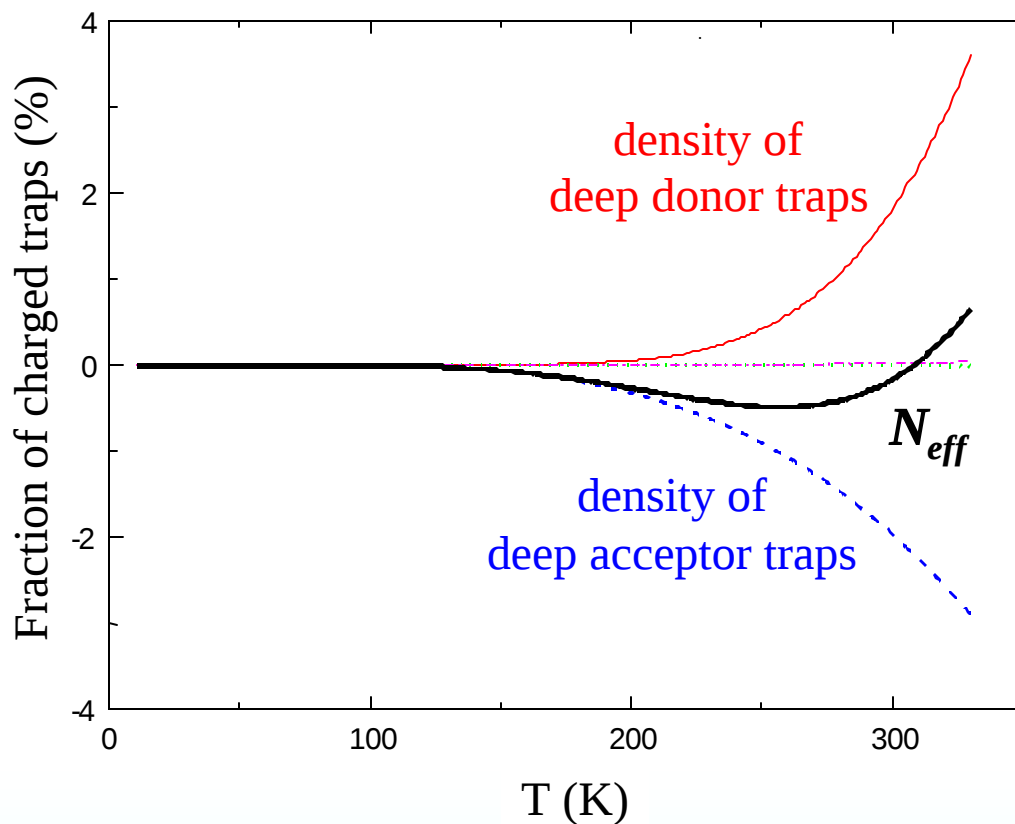


300 μm + 10^{15} n/cm^2
130 K + 250 V
 p 5'000 e^-



The Lazarus Effect

- *There is no comprehensive model yet...*



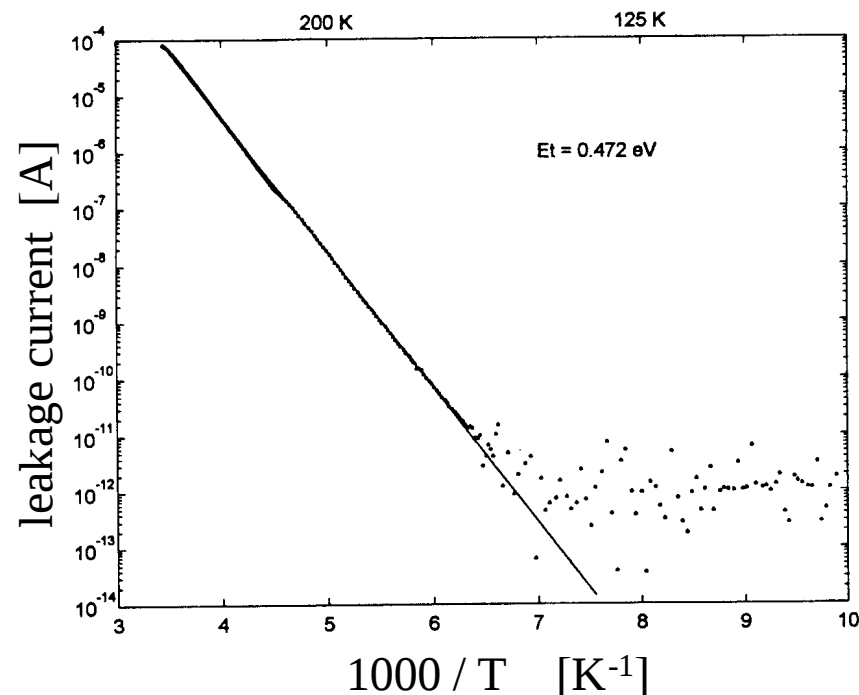
- By cooling, we manipulate the Si bulk properties
- Most relevant:
 - ✓ charge carrier density
 - ✓ [de-]trapping probability
- Cooling → fraction of charged traps decreases
→ $|N_{eff}|$ decreases

Elena Verbitskaya et al., RD39 Coll. Meeting, March 2001.

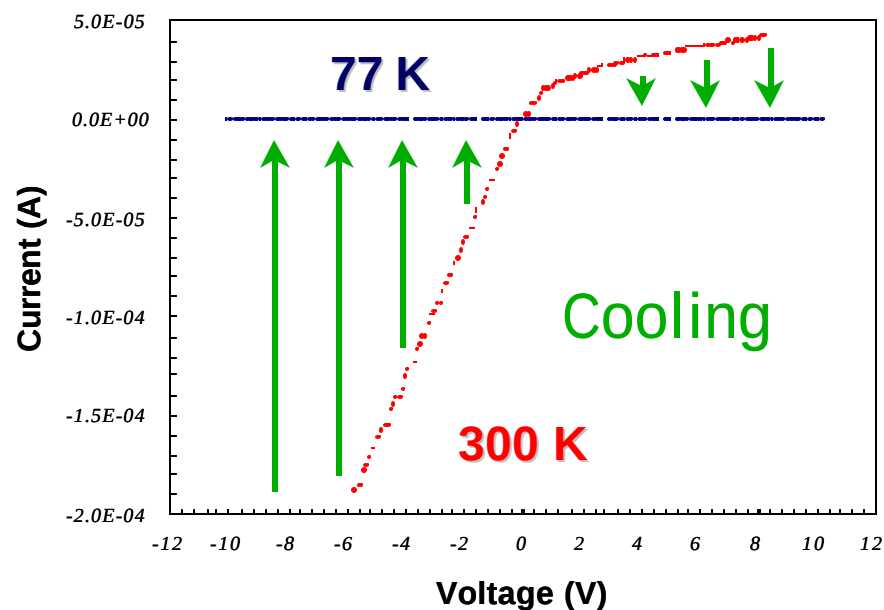


Leakage Current vs Temperature

Exponential Decrease of Leakage Current



Irradiated detector



$I < 1$ nA up to ± 500 V !

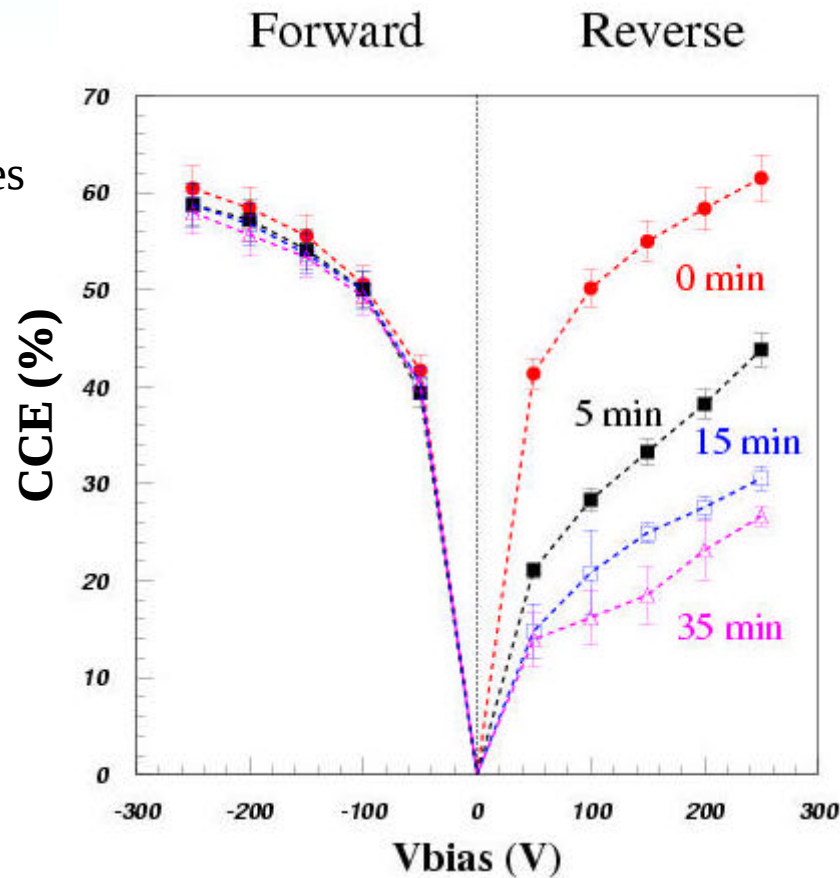
- low noise
- no power dissipation in the sensor



Forward Bias Operation

RD39 data
irradiated Si diodes
exposed to mips

$T = 78 \text{ K}$



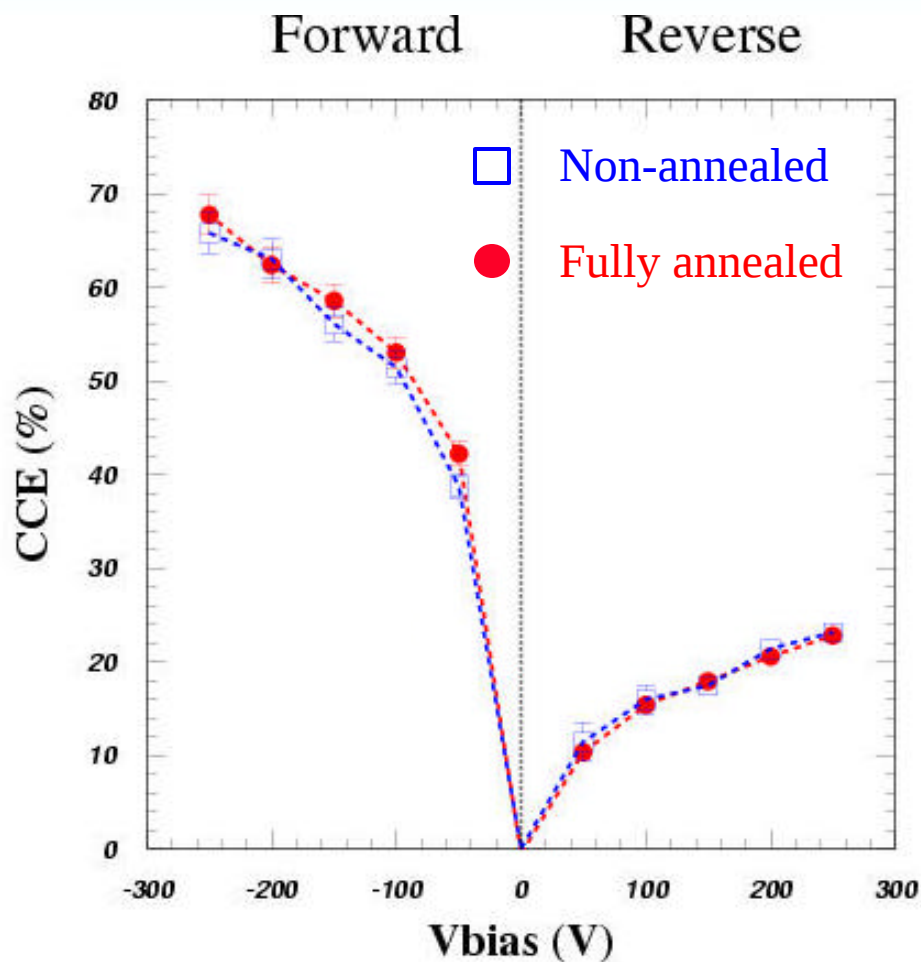
- **Reverse bias:**
CCE decreases with time
- **Forward bias:**
no time evolution !

$300 \mu\text{m} + 10^{15} \text{ n/cm}^2 @ 130 \text{ K} @ 250 \text{ V } P 15'000 e^-$



What about Annealing?

RD39 data
 10^{15} n/cm^2



The CCE at cryogenic temperatures does not depend on the annealing status of the detector

→ need to cool only during operation !!!



260 K vs 130 K

260 K

130 K

- Leakage current

→ detector noise

OK @ $>10^{14}$ n/cm²

OK @ $>10^{15}$ n/cm²

→ power in the sensor

~100μW/mm²

~1μW/mm²

- CCE (trapping + depletion)

reverse bias

3×10^{14} n/cm² :

65% @ 500V

100% @ 250V

2×10^{15} n/cm² :

0%

20% @ 250V

forward bias

2.8×10^{14} n/cm² :

70% @ 50V
(I = 6μA / mm²)

1×10^{15} n/cm² :

70% @ 250V
(I < 1nA / 5×5mm²)

- Annealing:

need to keep the
detector at -10°C

cooling only
during operation

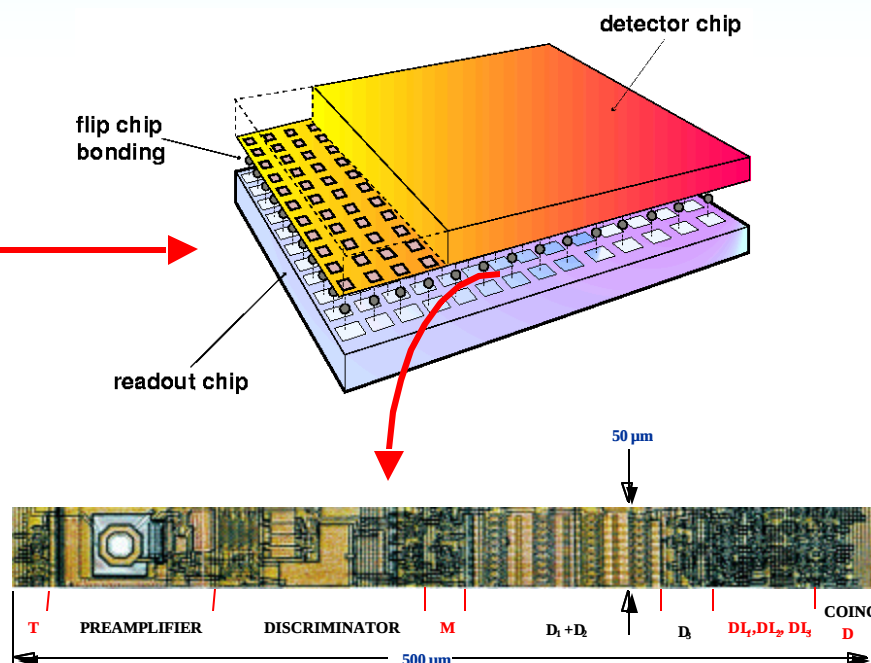
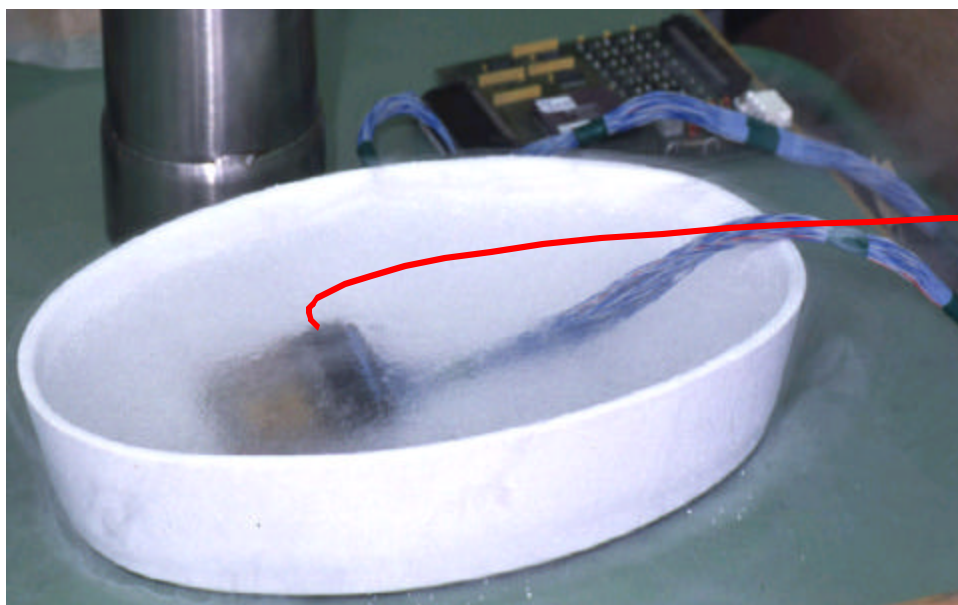


Don't be Afraid of Operating a Si Detector at Cryogenic Temperatures !



Cold Pixel Lasagna

RD19/WA97 LHC1 Pixel Detector



- CMOS 1µm technology, 2048 cells, $50 \times 500 \mu\text{m}^2$, 800 000 transistors
- Designed for RT operation, we managed to operate it at 77 K
80% of the channels OK
Average threshold: **7000 e⁻ @ 300K**, **2500 e⁻ @ 77K**
(also Alice2Test and APV25, 0.25 µm technology)
- Several thermal cycles: wire-bonding, bump-bonding, etc. OK !
- Simple tests can be done by immersing into liquid nitrogen...



Designing a Cryogenic Tracker

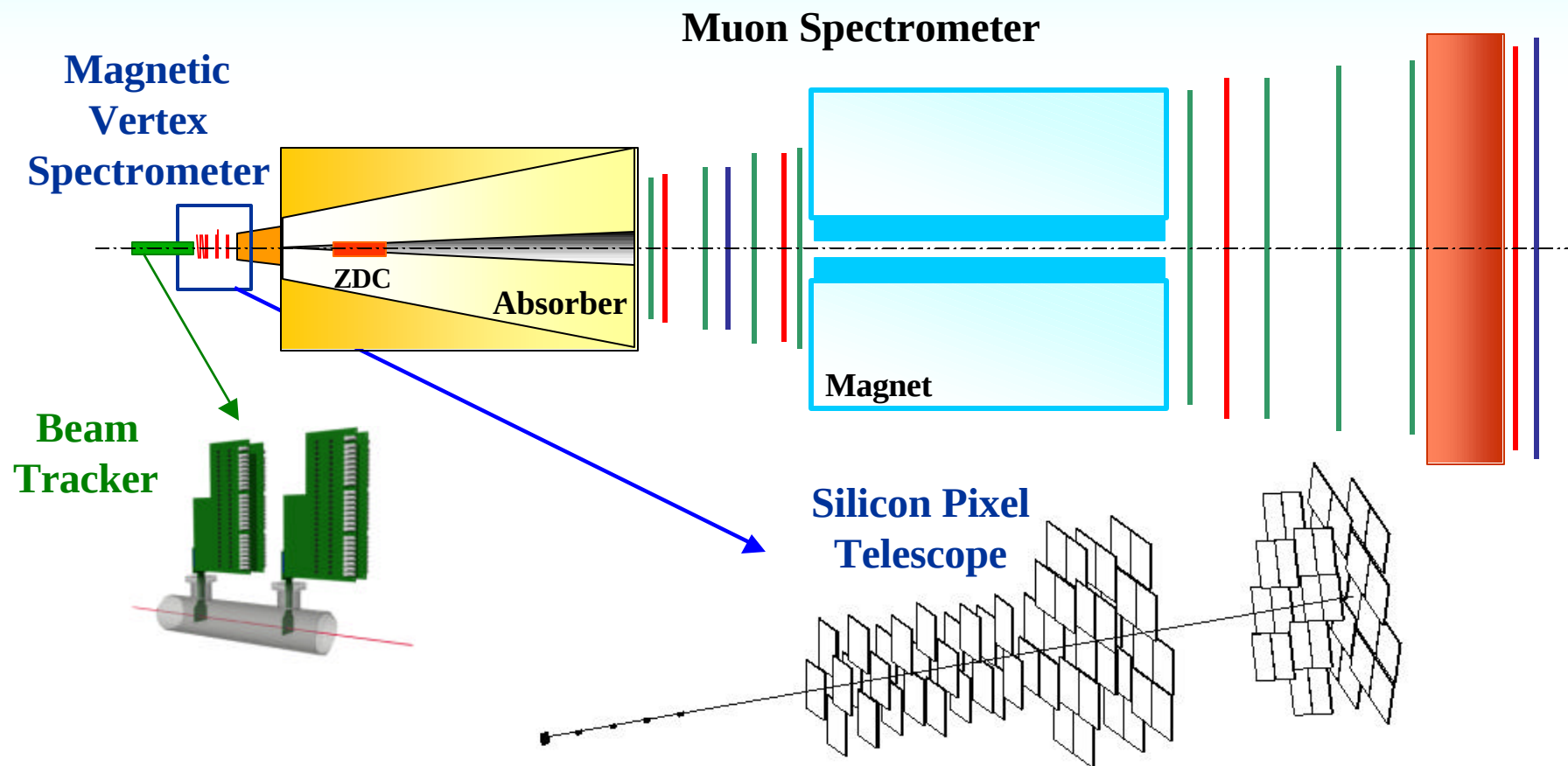
- More attention to the choice of all materials
(for example: thermal expansion of epoxy...)
- Important: cooling must be integrated into
mechanics design and should not be an add on
(always true...)
- Nature helps: Si thermal conductivity increases
with decreasing temperature
use Si as substrate: also matches the thermal
expansion of the detector...
- Two-phase nitrogen is an excellent coolant



The first application: Cryogenic Heavy Ion Beam Tracker for the NA60 Experiment



The NA60 Experiment

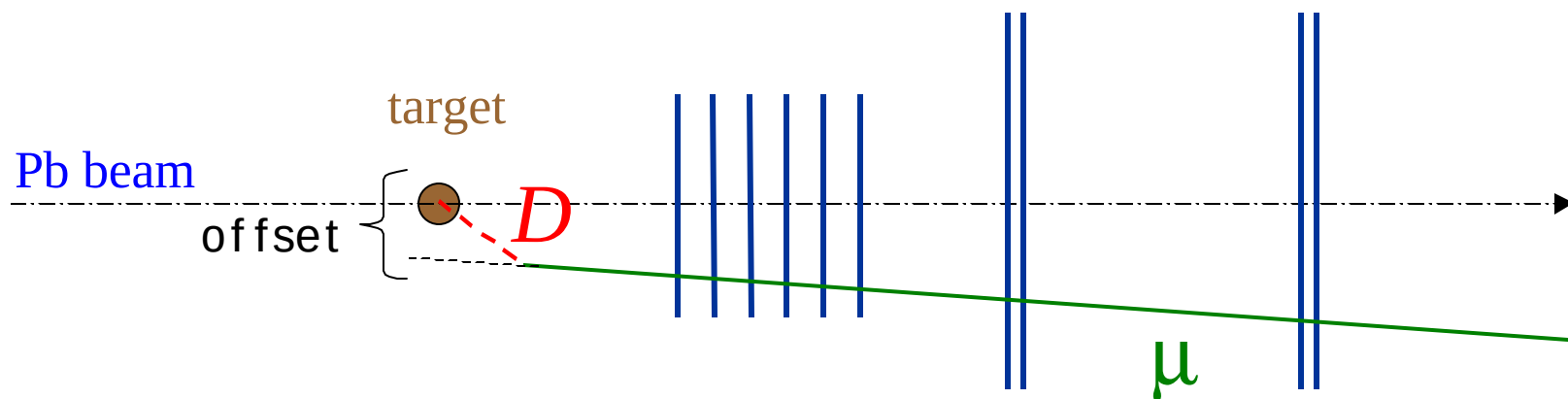


- Study $\mu^+\mu^-$ production in **heavy ion** collisions
- Signals related to phase transition from hadronic matter to Quark-Gluon Plasma
- First measurement of **charm production** in heavy ion collision



Charm Measurement in NA60

Silicon Pixel Telescope

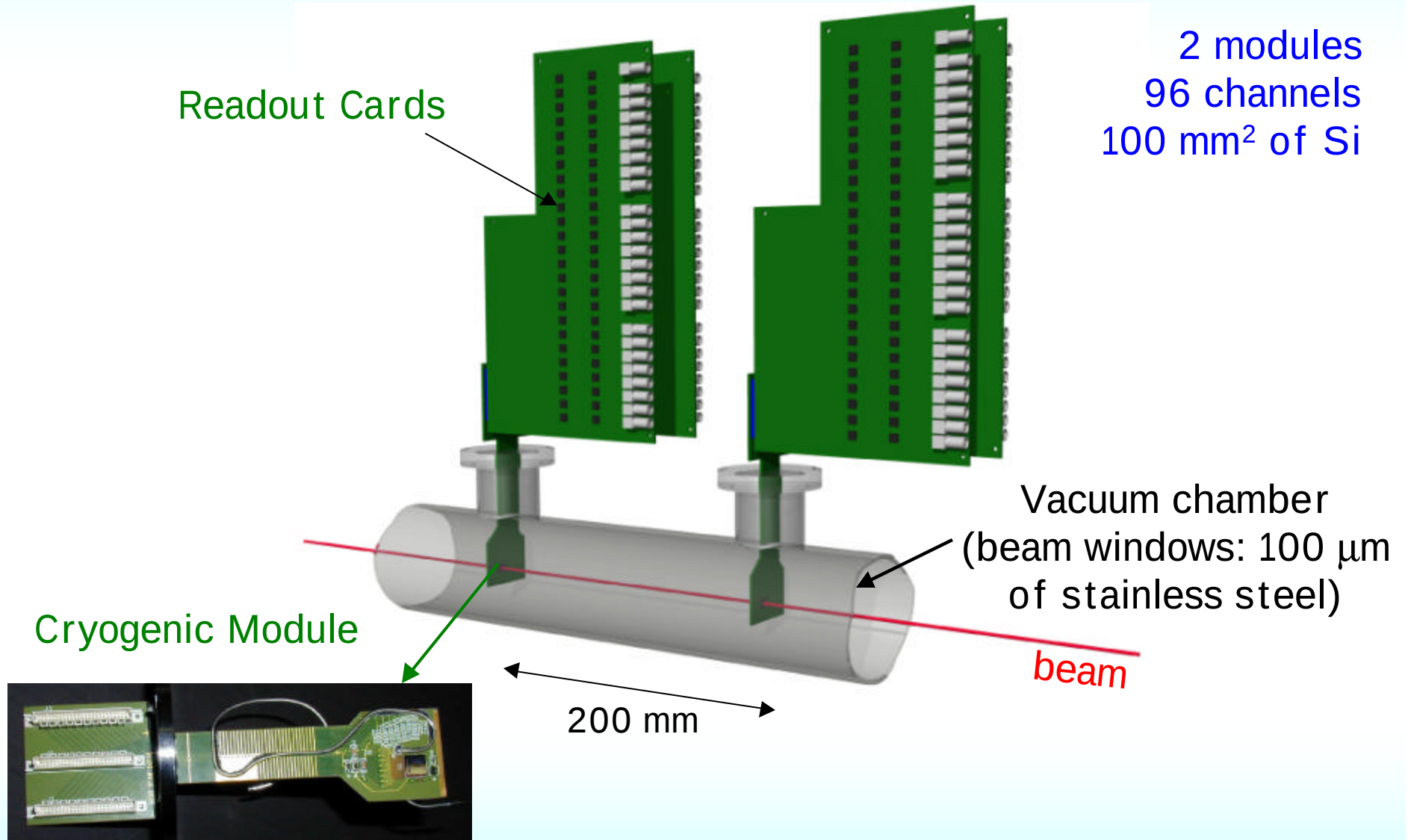


Need to measure the transverse coordinates of the interaction point

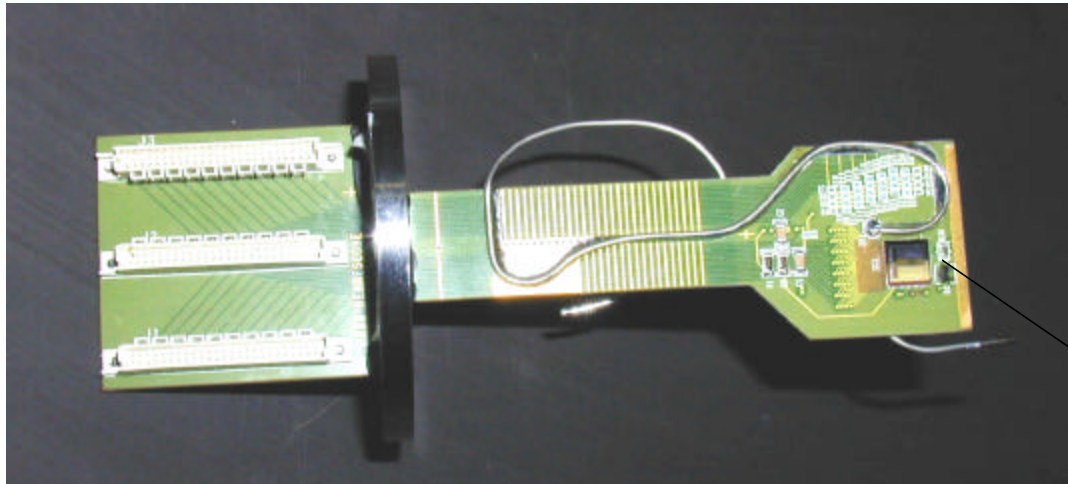
- ✓ Good position resolution: $\sim 20 \mu\text{m}$
- ✓ Good timing: two-pulse resolution $\sim 5 \text{ ns}$
- ✓ Extreme radiation hardness: $\sim 100 \text{ Grad}$



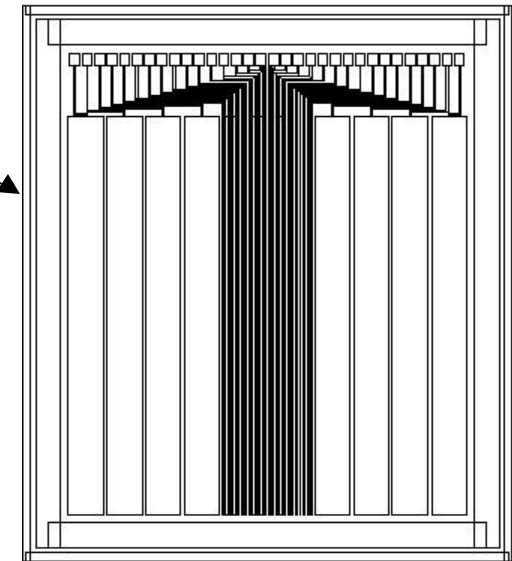
The Beamscope



The Cryogenic Module



Double-sided
glass-epoxy PCB



- Low mass cooling pipe ($\varnothing = 1\text{mm}$, $100\mu\text{m}$ thick)
- Integrated thermo-electrical design
 - ✓ power layers are meshed $\rightarrow$ reduces **longitudinal** conductivity
 - ✓ patterning of ground layer $\rightarrow$ improves **transverse** conductivity
- Temperature between 80K and 300K by adjusting LN_2 flow and heater power

- 24 narrow strips
(50 mm pitch)
- 2 x 4 wide strips
(500 mm pitch)



NA60 Beamscope Test, Fall 2000

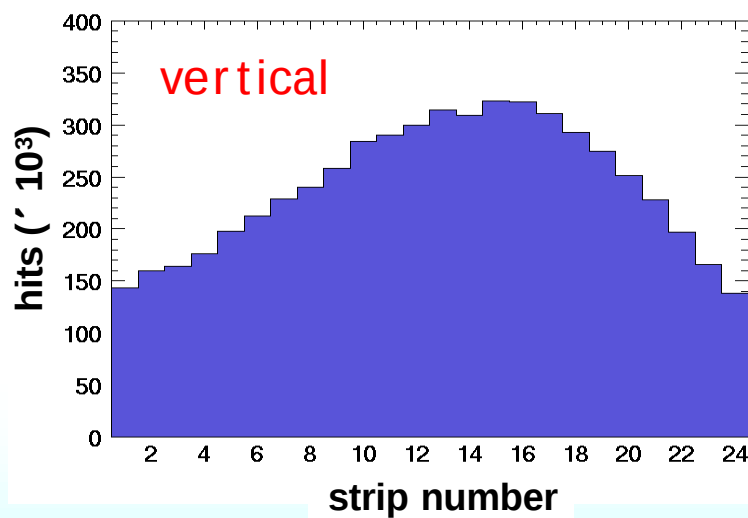
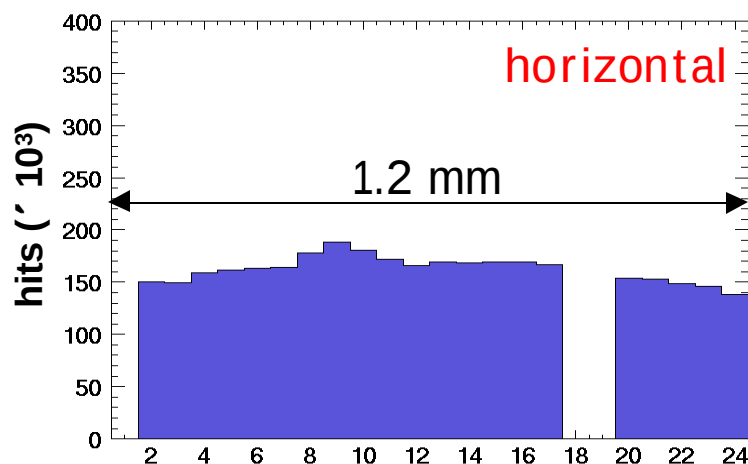
Exposed ~40 days to the 158 A GeV Pb beam

- *Average beam intensity: $7 \cdot 10^7$ ions per 4.5 s burst*
- *Total fluence: $5 \pm 2 \cdot 10^{14}$ ions/cm² (90 ± 40 Grad)*

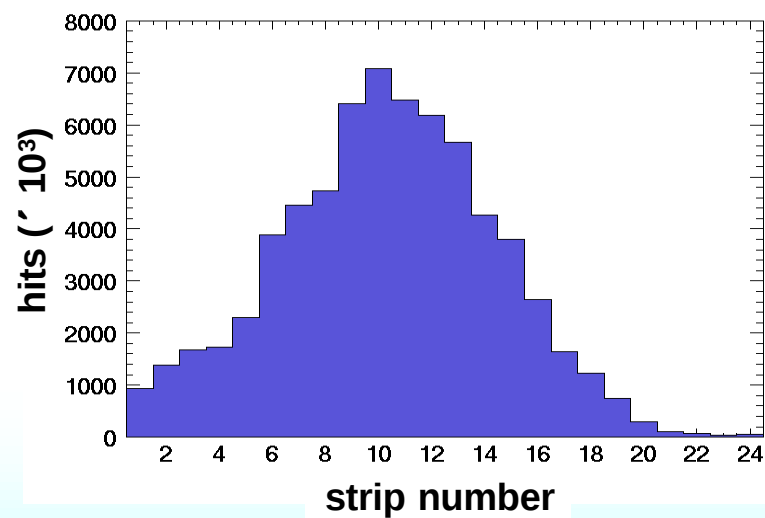
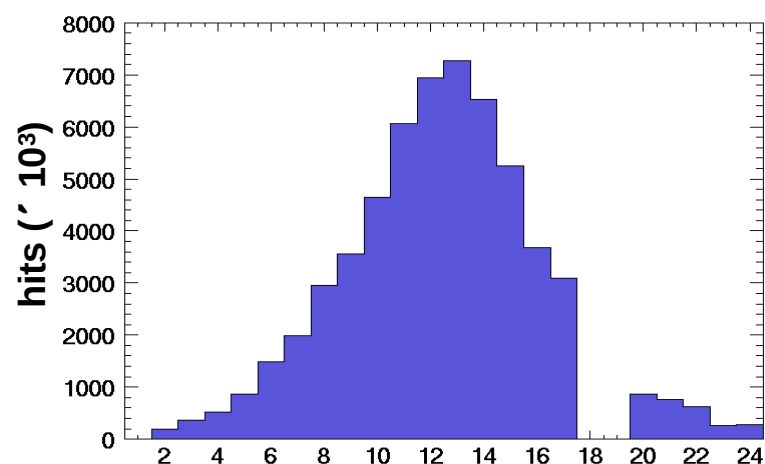


Beam Profile

Day 1



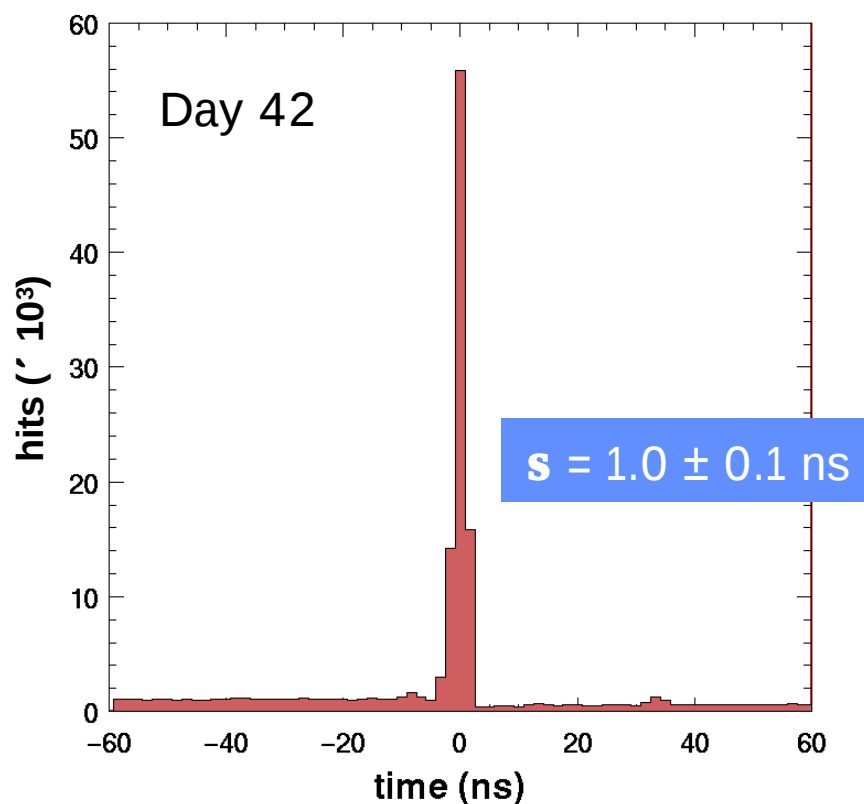
Day 38 (~85 Grad)



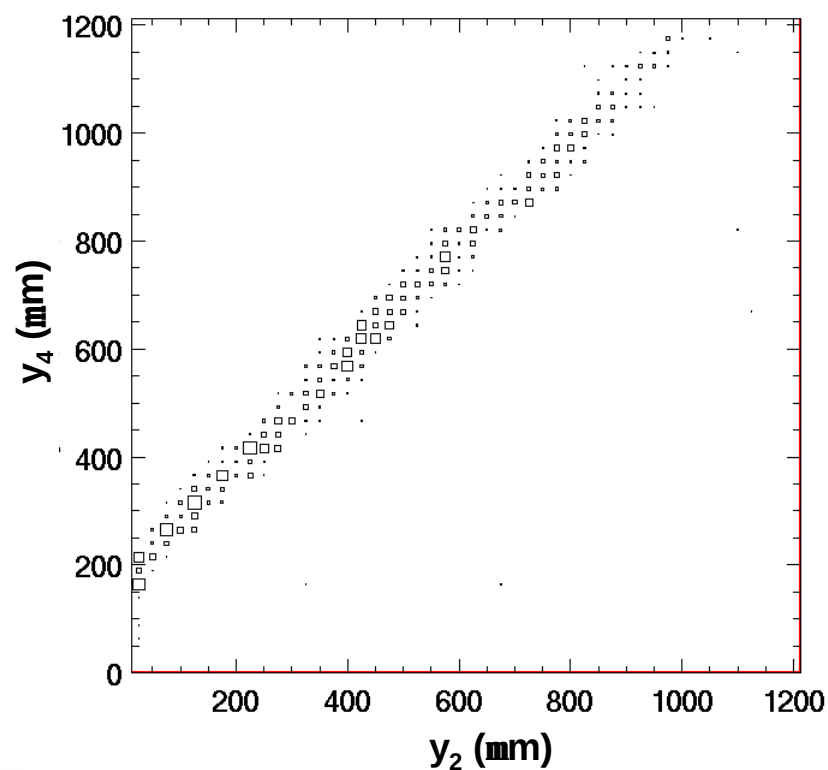


MHTR Timing & Cluster Correlation

Time of arrival wrt the trigger
of the hits in all strip integrated
over several spills, normalizing to
the same mean time.



Correlation of clusters in plane 2
and 4 (only hits within 3σ)

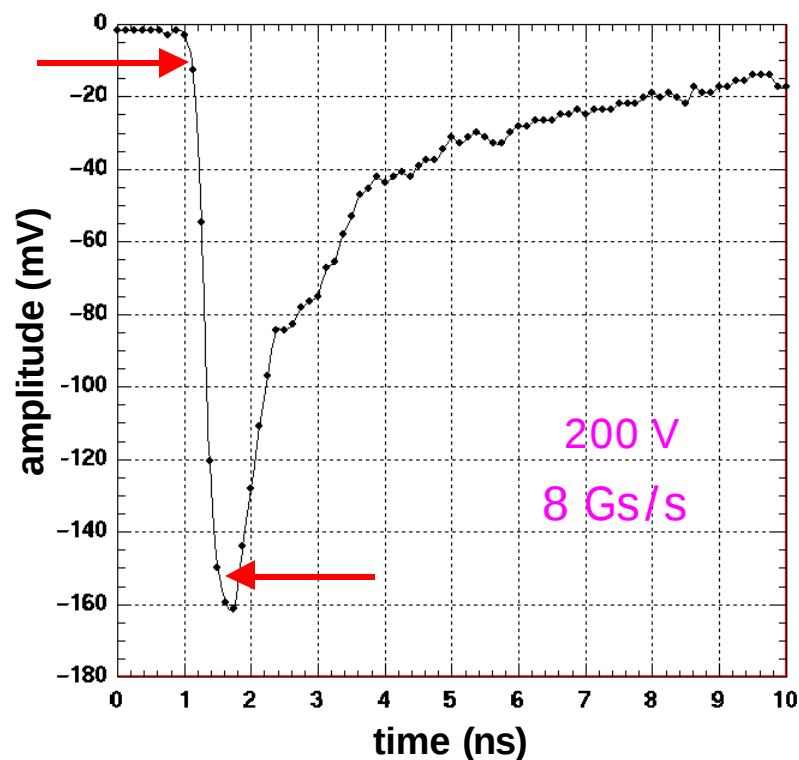


~ 200 μm misalignment



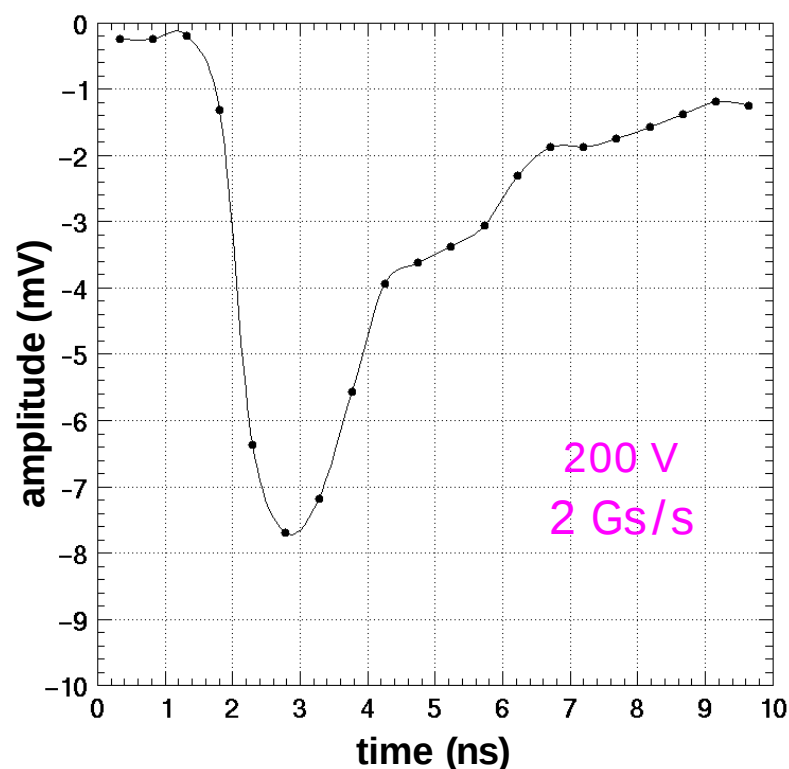
True (unshaped) Pb Ion Signal

Non-irradiated



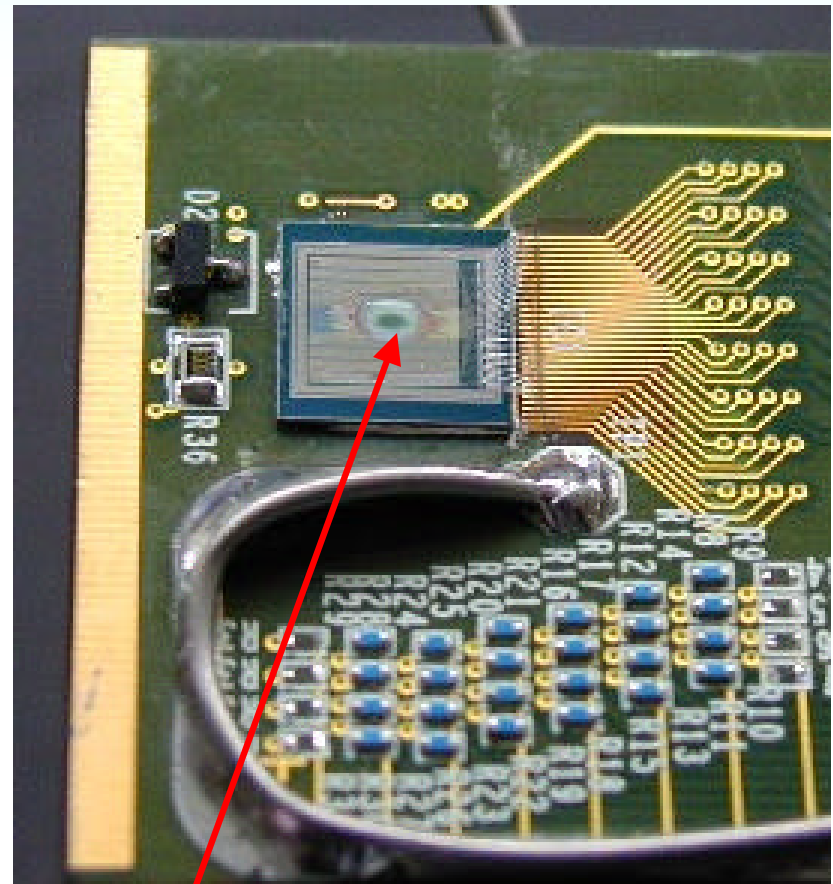
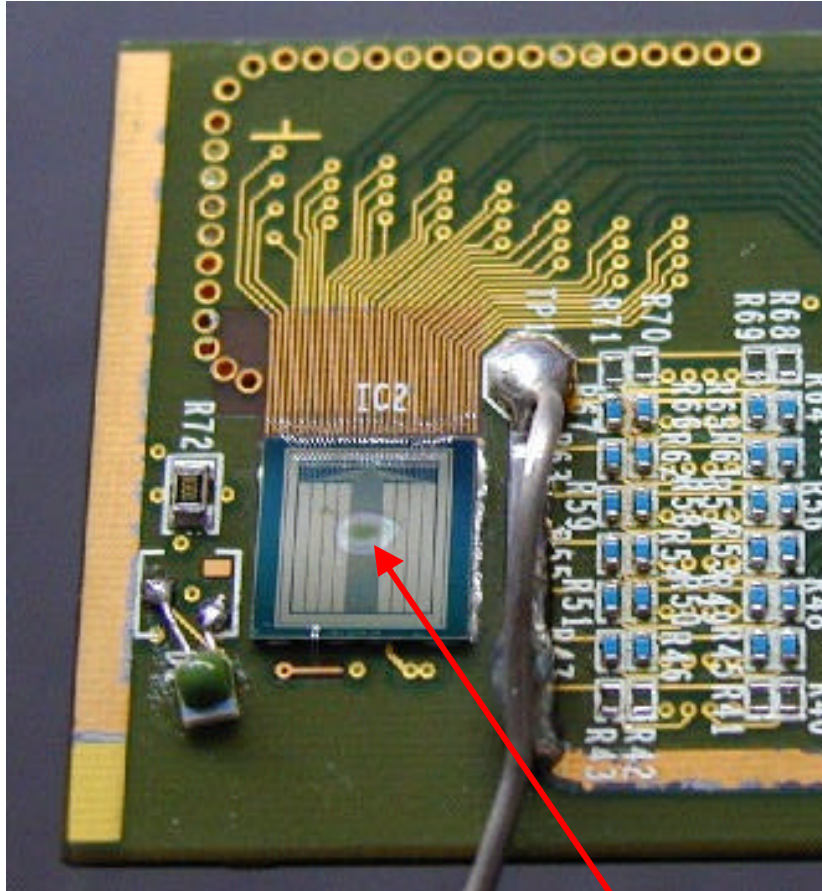
- Very fast rise time ($< 500\text{ps}$)
- Very long tail ($\sim 20\text{ns}$)

After 20 days (40 ± 20 Grad)



- Signal is broader
- Amplitude ~ 20 times lower...
but we see it !

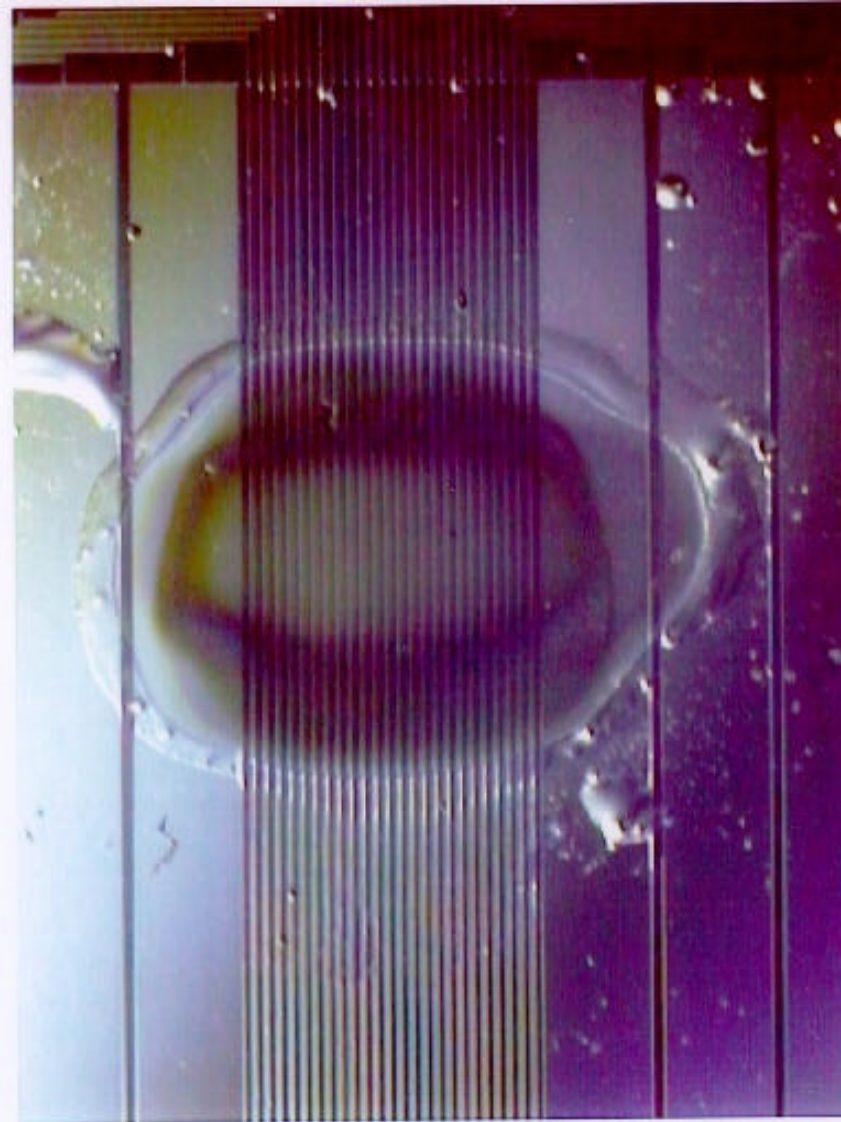
The Beamscope After 90 Grad



Pb beam's signature



The Beamscope After 90 Grad





Q&A Issues

Mechanical properties

- ✓ some defects may be tolerable at cryogenic temperatures

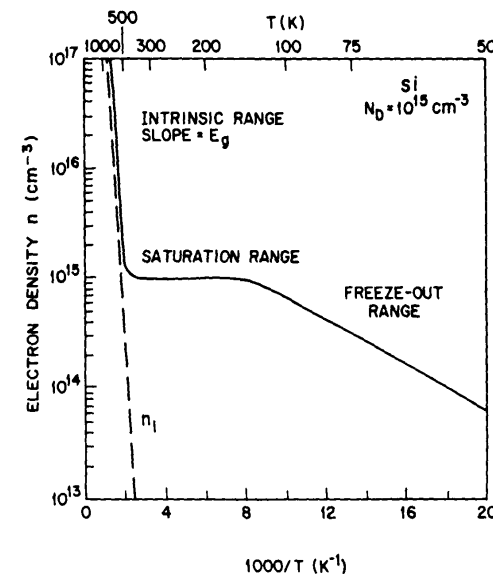
Electrical properties

- ✓ Leakage Current: suppressed at cryogenic T
(note: some nasty surface currents remains...)
- ✓ Depletion Voltage: lower at cryogenic T

⇒ *if detector is good @ 300K → better @ 130K*
bad @ 300K → may be good @ 130K

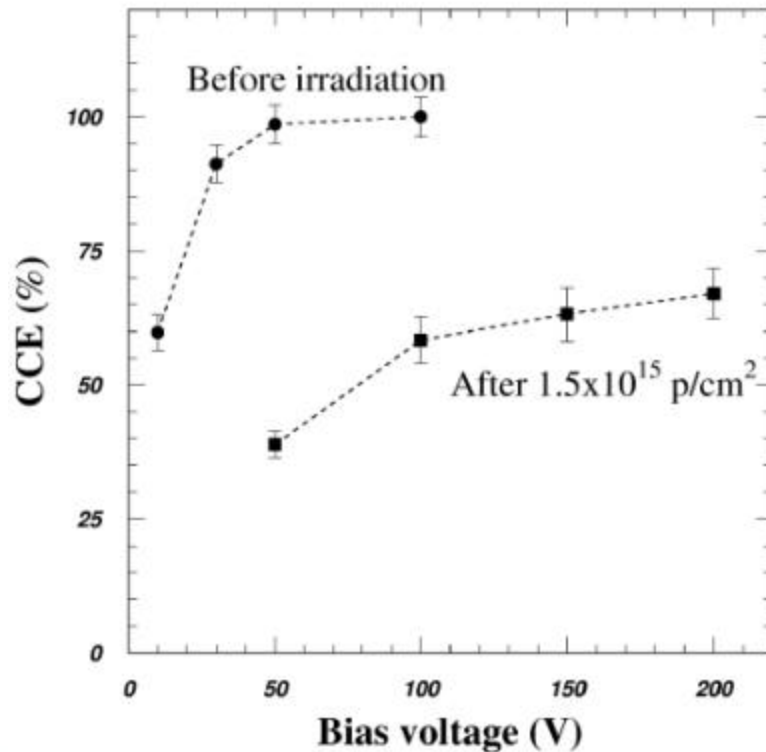
- ✓ Strip quality: DC coupling can be used
→ simpler detector processing

⇒ *no special testing required for a cold tracker (except for bad detectors)*
⇒ *higher yield*



RD39 data

Si pads irradiated @ 83 K
with 450 GeV protons



→ no significant differences
compared to room temperature !

Irradiation tests

- ✓ for characterization is OK to irradiate at RT and measure CCE in the cold
- ✓ no need for annealing studies



Conclusions

- Work to be done to understand the detail of the phenomenon. Nevertheless, data clearly show that **Cryogenic Operation** is a robust technique to **extend the lifetime** of Si trackers by more than one order of magnitude
- For heavy ions, where very large signals are obtained, Cryogenic Silicon can work up to **several tens of Grad**
- Thermal design for operation at 130 K is NOT more difficult than that for -10°C
- QA for a Cryogenic Tracker does not seem to require a more complicated testing procedure
- Future:
 - ✓ Cryogenic Detectors for **TOTEM**
 - ✓ Vertex Tracker of **COMPASS**
 - ✓ Beamscope for **NA60**

CERN-MIC developed a new CMOS readout chip to work at 130 K to track the proton beam